SLG59M309V



Ultra-small 7.8 mΩ 4 A Load Switch

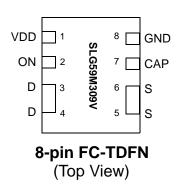
General Description

The SLG59M309V is a 7.8 m Ω 4 A single-channel load switch that is able to switch 1 to 5 V power rails. The product is packaged in an ultra-small 1.5 x 2.0 mm package.

Features

- 1.5 x 2.0 mm FC-TDFN 8L package (2 fused pins for drain and 2 fused pins for source)
- Logic level ON pin capable of supporting 0.85 V CMOS Logic
- User selectable ramp rate with external capacitor
- 7.8 m Ω RDS_{ON}while supporting 4 A
- Two Over Current Protection Modes
 - Short Circuit Current Limit
 - Active Current Limit
- Over Temperature Protection
- Pb-Free / Halogen-Free / RoHS compliant
- Operating Temperature: -40 °C to 85°C
- Operating Voltage: 2.5 V to 5.5 V

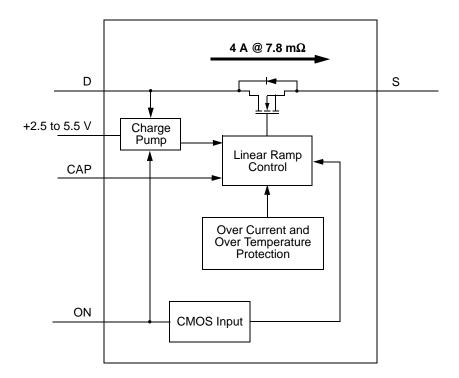
Pin Configuration



Applications

- Notebook Power Rail Switching
- Tablet Power Rail Switching
- Smartphone Power Rail Switching

Block Diagram





Pin Description

Pin #	Pin Name	Туре	Pin Description
1	VDD	PWR	VDD power for load switch control (2.5 V to 5.5 V)
2	ON	Input	Turns MOSFET ON (4 M Ω pull down resistor) CMOS input with VIL < 0.3 V, VIH > 0.85 V
3	D	MOSFET	Drain of Power MOSFET (fused with pin 4)
4	D	MOSFET	Drain of Power MOSFET (fused with pin 3)
5	S	MOSFET	Source of Power MOSFET (fused with pin 6)
6	S	MOSFET	Source of Power MOSFET (fused with pin 5)
7	CAP	Input	Capacitor for controlling power rail ramp rate
8	GND	GND	Ground

Ordering Information

Part Number	Туре	Production Flow		
SLG59M309V	FC-TDFN 8L	Industrial, -40 °C to 85 °C		
SLG59M309VTR	FC-TDFN 8L (Tape and Reel)	Industrial, -40 °C to 85 °C		



SLG59M309V

Absolute Maximum Ratings

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit				
V _{DD}	Power Supply				7	V				
T _S	Storage Temperature		-65		150	°C				
ESD _{HBM}	ESD Protection	Human Body Model	2000			V				
W _{DIS}	Package Power Dissipation				1	W				
MOSFET IDS _{PK}	Peak Current from Drain to Source	For no more than 1 ms with 1% duty cycle			6	А				
Note: Stresses gre	Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating									

only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics

 T_A = -40 °C to 85 °C (unless otherwise stated)

oply Voltage oply Current (PIN 1) n to Source ance Current age lay Time	-40 °C to 85 °C when OFF when ON, No load $T_A 25^{\circ}C @ 100 mA$ $T_A 70^{\circ}C @ 100 mA$ $V_D = 1.0 V to 5.5 V$	2.5 	 70 7.8 8.5	5.5 1 100 9.5	V μΑ μΑ mΩ
n to Source ance Current age	when ON, No load T _A 25°C @ 100 mA T _A 70°C @ 100 mA		70 7.8	100	μA
n to Source ance Current age	T _A 25°C @ 100 mA T _A 70°C @ 100 mA		7.8		
ance Current age	T _A 70°C @ 100 mA			9.5	mΩ
Current	··		8.5		
ige	V _D = 1.0 V to 5.5 V			11.5	mΩ
0				4	А
lay Time		1.0		V _{DD}	V
	50% ON to Ramp Begin	0	300	500	μs
	50% ON to 90% V_S	Co	onfigurable	e ¹	ms
On Time	Example: CAP (PIN 7) = 4 nF, V_{DD} = V_D = 5 V, Source_Cap = 10 μ F, IDS = 100 mA		1.96		ms
	10% $V_{\rm S}$ to 90% $V_{\rm S}$	Configurable		e ¹	V/ms
	Example: CAP (PIN 7) = 4 nF, V_{DD} = V_D = 5 V, Source_Cap = 10 μ F, IDS = 100 mA		3.0		V/ms
р	Source to GND			500	μF
Voltage on ON pin		0.85		V _{DD}	V
Voltage on ON pin		-0.3	0	0.3	V
rent Limit	MOSFET will automatically limit cur- rent when VS > 250 mV		6.0		А
uit Current Limit	MOSFET will automatically limit cur- rent when VS < 250 mV		0.5		А
nutoff turn-on temperature			125		°C
nutoff turn-off temperature			100		°C
nutoff time				1	ms
	50% ON to V_S Fall, $V_{DD} = V_D = 5 V$		20	28	μs
יר	utoff turn-on temperature utoff turn-off temperature	it Current Limit rent when VS < 250 mV	it Current Limit rent when VS < 250 mV	it Current Limit rent when VS < 250 mV	It Current Limitrent when VS < 250 mV0.5utoff turn-on temperature125utoff turn-off temperature100utoff time10



SLG59M309V Turn ON

The normal power on sequence is first VDD, with VD only being applied after VDD is > 1 V, and then ON after VD is at least 90% of final value. The normal power off sequence is the power on sequence in reverse.

If VDD and VD are turned on at the same time then it is possible that a voltage glitch will appear on VS before VDD achieves 1V which is the VT of the main MOSFET. The size of the glitch is dependent on source and drain capacitance loading and the ramp rate of VDD & VD.

SLG59M309V Turn ON

The VS ramp follows a linear path, not an RC limitation provided the ramp is slow enough to not be current limited by load capacitance.

SLG59M309V Current Limiting

The SLG59M309V has two forms of current limiting.

Standard Current Limiting Mode

Current is measured by mirroring the current through the main MOSFET. The mirrored current is then sent through a resistor creating a voltage V(i) proportional to the MOSFET current. The V(i) is then compared with a Band Gap voltage V(BG). If V(i) exceeds the Band Gap voltage then the voltage V(g) on the gate of the main MOSFET is reduced. The V(g) continues to drop until V(i) < V(BG). This response is a closed loop response and is therefore very fast and current limits in less than a few micro-seconds. There is no difference between peak or constant current limit.

Temperature Cutoff

However, as the V(g) drops the Rds(ON) of the main MOSFET will increase, thus limiting the current, but also increasing the power dissipation of the IC. The IC is very small and cannot dissipate much power. Therefore, if a current limit condition is sustained the IC will heat up. If the temperature exceeds approximately 120°C, then V(g) will be brought low completely shutting off the main MOSFET. As the die cools the MOSFET will be turned back on at 100°C.

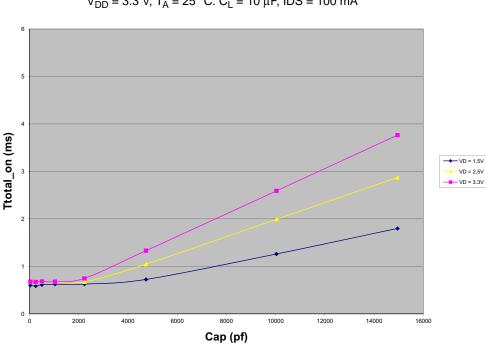
If the current limiting condition has not been mitigated then the die will again heat up to 120°C and the process will repeat.

Short Circuit Current Limiting Mode

When V(S) < 250 mV, which is the case if there is a solder bridge during the manufacturing process or a hard short on the power rail, then the current is limited to approximately 500 mA. This current limit is accomplished in the same manner as the Standard Current Limiting Mode with the exception that the current mirror is 15x greater. Because the current mirror is so much larger, a 15x smaller main MOSFET current is required to generate the same V(i). If V(S) rises above approximately 250 mV, then this mode is automatically switched out.

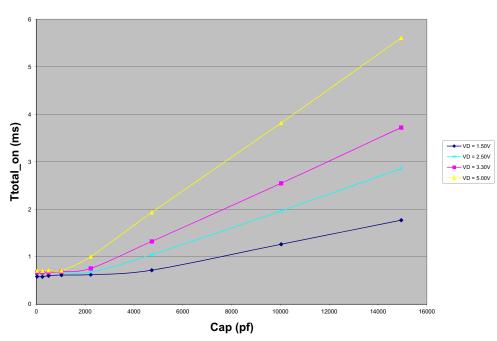


$T_{Total_{ON}}$ vs. CAP @ V_{DD} = 3.3 V



SLG59M309V T_{Total_ON}: ON (50%) - V_S (90%) V_{DD} = 3.3 V, T_A = 25 °C. C_L = 10 μ F, IDS = 100 mA

$T_{Total ON}$ vs. CAP @ V_{DD} = 5.0 V

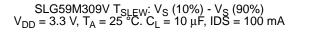


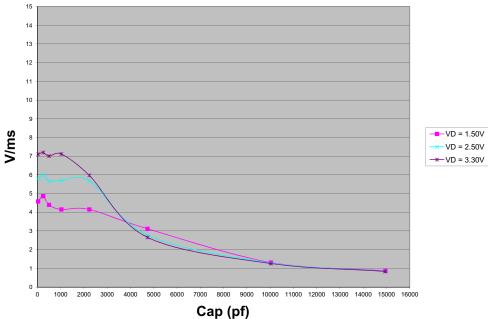
SLG59M309V T_{Total_ON}: ON (50%) - V_S (90%) V_{DD} = 5.0 V, T_A = 25 °C. C_L = 10 μ F, IDS = 100 mA



SLG59M309V

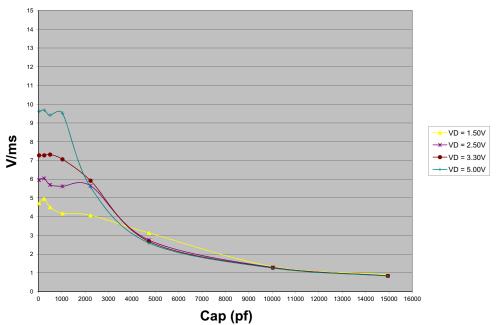
T_{SLEW} vs. CAP @ V_{DD} = 3.3 V





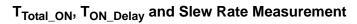


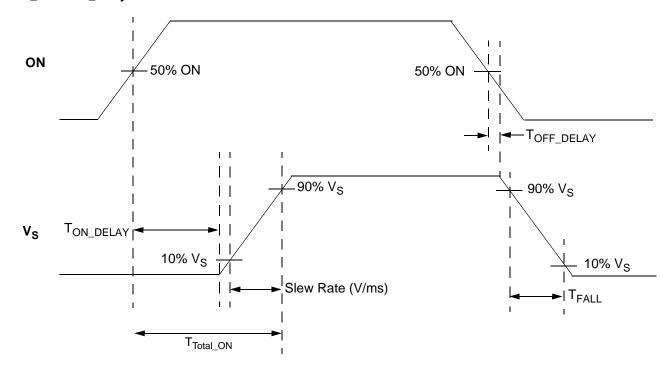
SLG59M309V T_{SLEW}: V_S (10%) - V_S (90%) V_{DD} = 5.0 V, T_A = 25 °C. C_L = 10 μ F, IDS = 100 mA





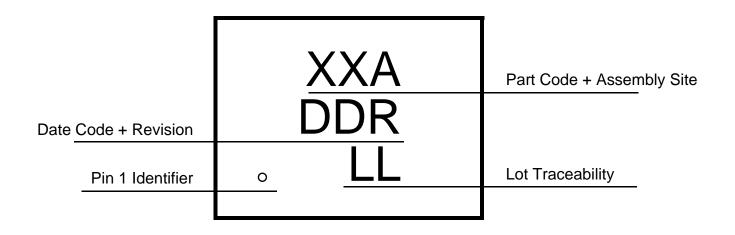
SLG59M309V





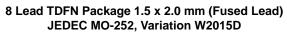


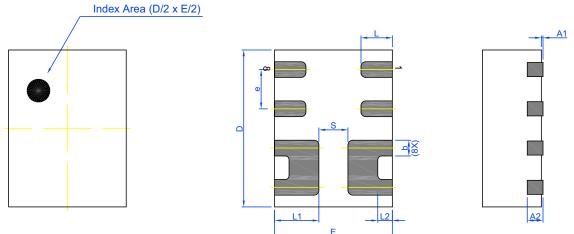
Package Top Marking System Definition





Package Drawing and Dimensions







Unit: mm										
Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max			
A	0.70	0.75	0.80	L	0.35	0.40	0.45			
A1	0.005	-	0.060	L1	0.515	0.565	0.615			
A2	0.15	0.20	0.25	L2	0.135	0.185	0.235			
b	0.15	0.20	0.25	е	0.50 BSC					
D	1.95	2.00	2.05	S	0.37 REF					
E	1.45	1.50	1.55							

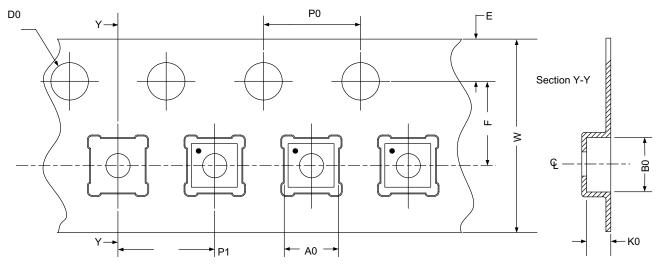


Tape and Reel Specifications

J	# of	Package Size	Max Units		Reel &	Leader (min)		Trailer (min)		Таре	Part
	Pins		per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
TDFN 8L FC Green	8	1.5 x 2.0 x 0.75	3000	3000	178 / 60	100	400	100	400	8	4

Carrier Tape Drawing and Dimensions

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width
	A0	В0	К0	P0	P1	D0	Е	F	w
TDFN 8L FC Green	1.68	2.18	0.9	4	4	1.5	1.75	3.5	8



Refer to EIA-481 specification

Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 2.25 mm³ (nominal). More information can be found at www.jedec.org.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Power Switch ICs - Power Distribution category:

Click to view products by Silego manufacturer:

Other Similar products are found below :

TCK111G,LF(SFPF1018DS1222TCK2065G,LFSZNCP3712ASNT3GMIC2033-05BYMT-T5MIC2033-12AYMT-T5MIC2033-05BYM6-T5SLG5NT1437VTRSZNCP3712ASNT1GDML1008LDS-7KTS1670EDA-TRKTS1640QGDV-TRKTS1641QGDV-TRNCV459MNWTBGFPF2260ATMXU6513AU6119SMIC2012YM-TRMAX14919ATP+MC33882PEPTPS2021IDRQ1TPS2104DBVRMIC2098-1YMT-TRMIC94062YMTTRMP6231DN-LFMIC2075-2YMMIC2095-2YMT-TRMIC94068YML-TRSIP32461DB-T2-GE1NCP335FCT2GTCK105G,LF(SAP2151DSG-13MIC94094YC6-TRMIC94064YC6-TRMIC2505-1YMMIC94305YMT-TRMIC94081YFT-TRMIC94042YFL-TRMIC94041YFL-TRMIC2005-1.2YM6-TRTPS2032QDRQ1SIP32510DT-T1-GE3NCP333FCT2GNCP331SNT1GTPS2063DRTPS2042PMIC2008YML-TRMIC2040-1YMM